


INFORMATION DISCLOSURE CITATION

Atty. Docket No.	04329.2343-02	Div. of Appln. No.	10/200,446 10810837
Applicant	Atsushi YAGISHITA et al.		
Filing Date	Herewith	Prior Group:	2823

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Examiner Initial*		Document Number	Issue Date	Name	Class	Sub Class	Filing Date If Appropriate
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Examiner		Date Considered	2/1/06
*Examiner:	Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.		
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